2N3905 / 2N3906

PNP Silicon Epitaxial Planar Transistor

for switching and amplifier applications.

As complementary types the NPN transistors 2N3903 and 2N3904 are recommended.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector TO-92 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	40	V
Collector Emitter Voltage	-V _{CEO}	40	V
Emitter Base Voltage	-V _{EBO}	6	V
Collector Current	-I _C	200	mA
Power Dissipation	P _{tot}	625	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C







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Characteristics at $T_a = 25 \ ^{\circ}C$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain	-			
at $-V_{CE} = 1 V$, $-I_C = 0.1 mA$ 2N3905	h _{FE}	30	-	-
2N3906	h _{FE}	60	-	-
at $-V_{CE} = 1 \text{ V}, -I_C = 1 \text{ mA}$ 2N3905	h _{FE}	40	-	-
2N3906	h _{FE}	80	-	-
at $-V_{CE} = 1 \text{ V}, -I_C = 10 \text{ mA}$ 2N3905	h _{FE}	50	150	-
2N3906	h _{FE}	100	300	-
at $-V_{CE} = 1 \text{ V}, -I_C = 50 \text{ mA}$ 2N3905	h _{FE}	30	-	-
2N3906	h _{FE}	60	-	-
at $-V_{CE} = 1 \text{ V}, -I_C = 100 \text{ mA}$ 2N3905	h _{FE}	15	-	-
2N3906	h _{FE}	30	-	-
Collector Base Cutoff Current			= 0	
at $-V_{CB} = 30 \text{ V}$	-I _{CBO}	-	50	nA
Emitter Base Cutoff Current				
at $-V_{EB} = 6 V$	-I _{EBO}	-	50	nA
Collector Base Breakdown Voltage	-V _{(BR)CBO}	40	-	V
at -I _C = 10 μA	• (BR)CBO			•
Collector Emitter Breakdown Voltage	N/	10		N/
at -I _c = 1 mA	-V _{(BR)CEO}	40	-	V
Emitter Base Breakdown Voltage				
at $-I_E = 10 \ \mu A$	-V _{(BR)EBO}	6	-	V
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Collector Emitter Saturation Voltage				
at $-I_{C} = 10 \text{ mA}, -I_{B} = 1 \text{ mA}$	-V _{CE(sat)}	-	0.25	V
at $-I_{C} = 50 \text{ mA}, -I_{B} = 5 \text{ mA}$	-V _{CE(sat)}	-	0.4	
Base Emitter Saturation Voltage				
at $-I_c = 10$ mA, $-I_B = 1$ mA	-V _{BE(sat)}	-	0.85	V
at $-I_c = 50$ mA, $-I_B = 5$ mA	-V _{BE(sat)}	_	0.95	v
	• BE(sat)		0.00	
Gain Bandwidth Product				
at $-V_{CE} = 20 \text{ V}, -I_C = 10 \text{ mA}, \text{ f} = 100 \text{ MHz}$ 2N3905	f⊤	200	-	MHz
2N3906		250	-	
Collector Base Capacitance	_			_
at $-V_{CB} = 5 \text{ V}, \text{ f} = 100 \text{ KHz}$	C _{ob}	-	4.5	pF
	+			
	t _d	-	35	ns
at $-V_{CC} = 3 V$, $-V_{BE} = 0.5 V$, $-I_C = 10 mA$, $-I_{B1} = 1 mA$	-			
Rise Time	t _r		35	ns
at $-V_{CC} = 3 V$, $-V_{BE} = 0.5 V$, $-I_C = 10 mA$, $-I_{B1} = 1 mA$	ч	_		113
Storage Time			005	
at $-V_{CC} = 3 V$, $-I_C = 10 mA$, $-I_{B1} = I_{B2} = 1 mA$	t _s	-	225	ns
Fall Time	1			
	t _f	-	75	ns
at $-V_{CC} = 3 V$, $-I_C = 10 mA$, $-I_{B1} = I_{B2} = 1 mA$				

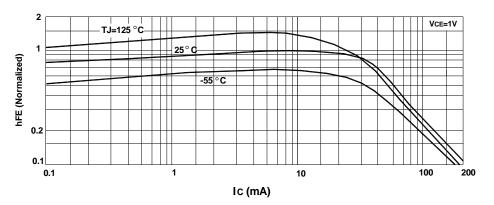


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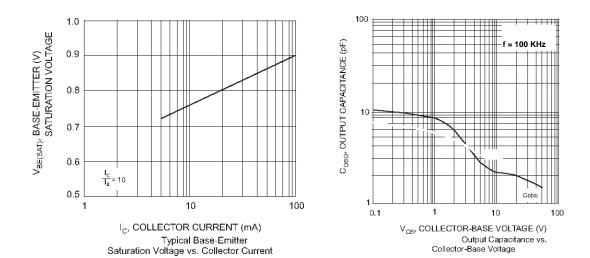
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DC Current Gain



Collector Saturation Region 1 TJ=25 30mA 0.8 100mA IC=1mA 0.6 Vce(V) 0.4 10mA 0.2 0 10 0.001 0.1 1







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